



#### **60V N-CHANNEL ENHANCEMENT MODE MOSFET**

100% Unclamped Inductive Switch (UIS) Test in Production

Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3)

Low R<sub>DS(ON)</sub> – Ensures On State Losses Are Minimized

## **Product Summary**

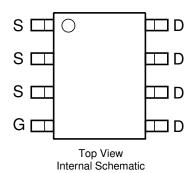
| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> max       | I <sub>D</sub> max<br>T <sub>A</sub> = +25°C |  |  |
|-------------------|-------------------------------|--|--|--|
| c0)/              | 9.5mΩ @ V <sub>GS</sub> = 10V | 10.8A  |  |  |
| 60V               | 12mΩ @ V <sub>GS</sub> = 4.5V | 9.6  |  |  |

# **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Power Management Functions
- DC-DC Converters
- Backlighting





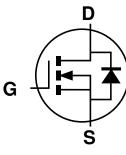
# Mechanical Data

**Features and Benefits** 

High Conversion Efficiency

Excellent Q<sub>gd</sub> x R<sub>DS(ON)</sub> Product (FOM) Advanced Technology for DC-DC Converters

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 <sup>(3)</sup>
- Weight: 0.074 grams (Approximate)



Equivalent circuit

## Ordering Information (Note 4)

| Part Number   | Case | Packaging         |
|---------------|------|-------------------|
| DMT6009LSS-13 | SO-8 | 2,500/Tape & Reel |

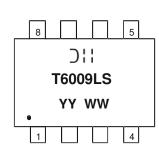
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



);; = Manufacturer's Marking T6009LS = Product Type Marking Code YYWW = Date Code Marking YY or  $\overline{YY}$  = Year (ex: 15 = 2015) WW = Week (01 to 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  |                 |  | Symbol           | Value        | Units |  |
|---|-----------------|--|------------------|--------------|-------|--|
| Drain-Source Voltage                                    |                 |  | V <sub>DSS</sub> | 60           | V     |  |
| Gate-Source Voltage                                     |                 |  | V <sub>GSS</sub> | ±20          | V     |  |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V | Steady<br>State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | ID               | 10.8<br>8.6  | A     |  |
|   | t<10s           | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | ID               | 14.4<br>11.5 | A     |  |
| Maximum Continuous Body Diode Forward Current (Note 6)  |                 |  | ls               | 3            | A     |  |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)      |                 |  | I <sub>DM</sub>  | 60           | А     |  |
| Avalanche Current, L = 0.1mH                            |                 |  | I <sub>AS</sub>  | 25           | А     |  |
| Avalanche Energy, L = 0.1mH                             |                 |  | E <sub>AS</sub>  | 31.5         | mJ    |  |

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                   |              | Symbol            | Value       | Units |
|--|--------------|-------------------|-------------|-------|
| Total Power Dissipation (Note 5)                 |              | PD                | 1.25        | W     |
| Thermal Resistance. Junction to Ambient (Note 5) | Steady State | Р                 | 100         | °C/W  |
| merinal Resistance, Junction to Ambient (Note 5) | t<10s        | R <sub>θ</sub> JA | 55.5        | °C/W  |
| Total Power Dissipation (Note 6)                 |              | PD                | 1.6         | W     |
| Thermal Desistance, Junction to Ambient (Nate 6) | Steady State | Б                 | 75          | °C/W  |
| Thermal Resistance, Junction to Ambient (Note 6) | t<10s        | R <sub>0</sub> JA | 42          | °C/W  |
| Thermal Resistance, Junction to Case (Note 6)    |              | $R_{\theta JC}$   | 12          | °C/W  |
| Operating and Storage Temperature Range          |              | TJ, TSTG          | -55 to +150 | °C    |

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

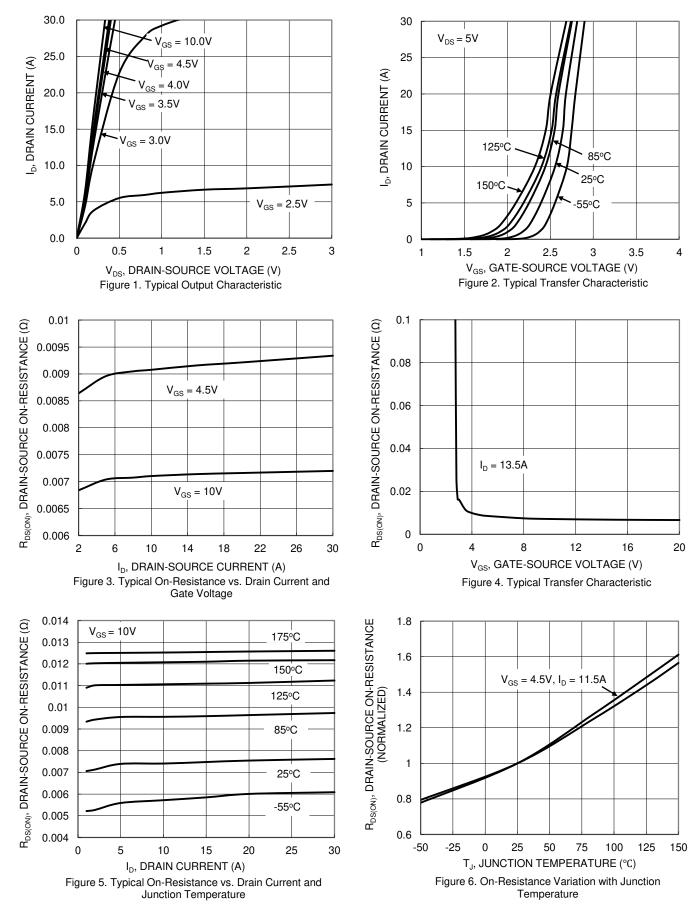
| Characteristic                             | Symbol               | Min | Тур   | Max  | Unit | Test Condition   |  |
|--|----------------------|-----|-------|------|------|--|--|
| OFF CHARACTERISTICS (Note 7)               | Symbol               |     | тур   | IWAA | Onit | Test condition   |  |
| Drain-Source Breakdown Voltage             | BV <sub>DSS</sub>    | 60  | -     | -    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA   |  |
| Zero Gate Voltage Drain Current            | IDSS                 | -   | -     | 1    | μA   | $V_{DS} = 48V, V_{GS} = 0V$  |  |
| Gate-Source Leakage                        | IGSS                 | -   | -     | ±100 | nA   | $V_{GS} = \pm 16V, V_{DS} = 0V$  |  |
| ON CHARACTERISTICS (Note 7)                |                      |     |       |      |      | <u> </u>   |  |
| Gate Threshold Voltage                     | V <sub>GS(TH)</sub>  | 0.7 | -     | 2    | V    | $V_{DS} = V_{GS}, I_D = 250 \mu A$   |  |
| Static Drain-Source On-Resistance          |                      | -   | 7.2   | 9.5  | mΩ   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 13.5A  |  |
| Static Drain-Source On-Resistance          | R <sub>DS</sub> (ON) | -   | 9     | 12   |      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 11.5A   |  |
| Diode Forward Voltage                      | V <sub>SD</sub>      | -   | 0.9   | 1.2  | V    | $V_{GS} = 0V, I_{S} = 20A$   |  |
| DYNAMIC CHARACTERISTICS (Note 8)           |                      |     |       |      |      |  |  |
| Input Capacitance                          | C <sub>iss</sub>     | -   | 1,925 | -    |      |  |  |
| Output Capacitance                         | Coss                 | -   | 438   | -    | pF   | $V_{DS} = 30V, V_{GS} = 0V,$<br>f = 1MHz   |  |
| Reverse Transfer Capacitance               | C <sub>rss</sub>     | -   | 41    | -    |      |  |  |
| Gate Resistance                            | R <sub>G</sub>       | -   | 1.7   | -    | Ω    | $V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$   |  |
| Total Gate Charge (V <sub>GS</sub> = 10V)  | Qg                   | -   | 33.5  | -    |      |  |  |
| Total Gate Charge (V <sub>GS</sub> = 4.5V) | Qg                   | -   | 15.6  | -    | nC   | $V_{DS} = 30V, I_D = 13.5A$  |  |
| Gate-Source Charge                         | Qgs                  | -   | 4.7   | -    | no   |  |  |
| Gate-Drain Charge                          | Q <sub>qd</sub>      | -   | 5.3   | -    |      |  |  |
| Turn-On Delay Time                         | t <sub>D(ON)</sub>   | -   | 4.5   | -    |      | $\label{eq:VDD} \begin{split} V_{DD} &= 30V, \ V_{GS} = 10V, \\ R_G &= 6\Omega, \ I_D = 13.5A \end{split}$ |  |
| Turn-On Rise Time                          | t <sub>R</sub>       | -   | 8.6   | -    |      |  |  |
| Turn-Off Delay Time                        | t <sub>D(OFF)</sub>  | -   | 35.9  | -    | ns   |  |  |
| Turn-Off Fall Time                         | tF                   | -   | 15.7  | -    |      |  |  |
| Body Diode Reverse Recovery Time           | t <sub>RR</sub>      | -   | 18.2  | -    | ns   |  |  |
| Body Diode Reverse Recovery Charge         | Q <sub>RR</sub>      | -   | 33.1  | -    | nC   | I <sub>F</sub> = 13.5A, di/dt = 400A/μs  |  |

 Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz. copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect. Notes:

8. Guaranteed by design. Not subject to product testing.



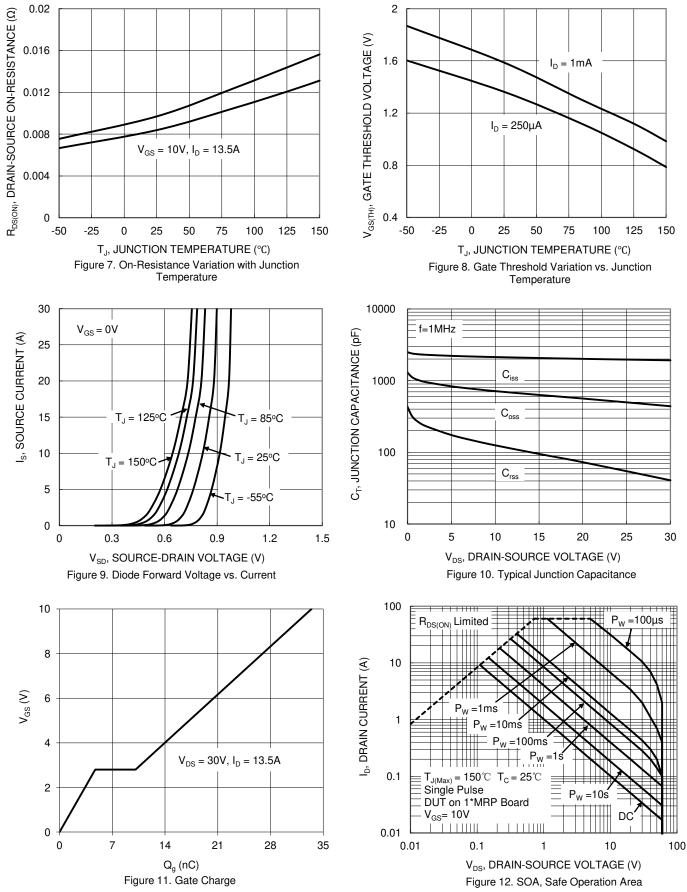
## DMT6009LSS



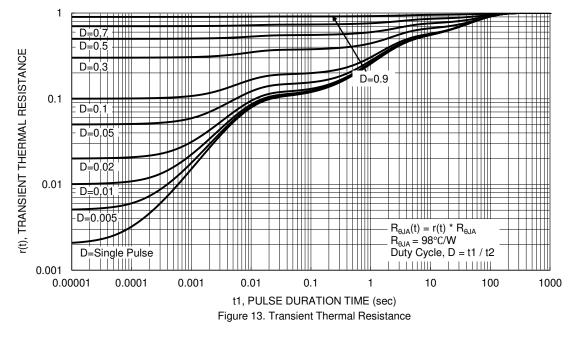
DMT6009LSS Document number: DS38289 Rev. 1 - 2



# DMT6009LSS

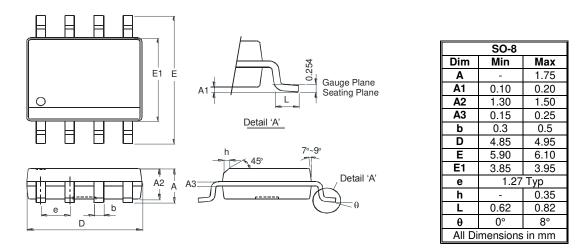






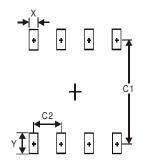
# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version



## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Х          | 0.60          |
| Y          | 1.55          |
| C1         | 5.4           |
| C2         | 1.27          |



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